

RECEIVED PAGE 05
CENTRAL FAX CENTER

MAR 05 2008

Docket No. PC 3216.01 US
USSN: 10/787,407PATENT
Art Unit: 1795

This listing of claims will replace all prior versions, and listings of claims in the application:

LISTING OF CLAIMS:

1. (Currently Amended) An electron beam recording substrate where electron beam information recording is carried out comprising:
 - a substrate main body;
 - a resist film relative to the substrate main body; and
 - ~~a surface layer area including at least two layers of thin film in between the substrate main body and the resist film, wherein the layer adjacent to the resist film has a smaller average distance λ than the layer adjacent to the substrate main body, the layers are made of materials a material containing at least one of elements with atomic numbers 21, 23, 25 to 36, 38 to 41, 43 to 48, 50 to 54, 56 to 72, 75 to 78, 80 and 82 to 83 by 50 wt% or greater that suppresses enlargement of a scattering distribution diameter of electrons spread inside by irradiation of an electron beam from a resist film side.~~
2. (Original) The electron beam recording substrate according to claim 1, wherein the substrate main body is positioned on a side opposite to said resist film with respect to said surface layer area.
3. (Original) The electron beam recording substrate according to claim 1, wherein said electron beam recording substrate is made only of a same material as said material for said surface layer area.

Docket No. PC 3216.01 US
USSN: 10/787,407

PATENT
Art Unit: 1795

4. - 5. (Cancelled)

6. (Currently Amended) The electron beam recording substrate according to claim 2, wherein each layer of the at least two layers of said surface layer area is made of a material containing at least one of elements with atomic numbers 73 to 79 by 50 wt% or greater and said substrate main body is made of a material containing at least one of elements with atomic numbers 13, 14, 21, 23, 25 to 36, 38 to 41, 43 to 48, 50 to 54, 56, 57, 72, 80 and [[80]] 82 to 83 by 50 wt% or greater.

7. (Original) The electron beam recording substrate according to claim 2, wherein said surface layer area is comprised of a plurality of thin films.

8. (Currently Amended) The electron beam recording substrate according to claim 7, wherein that thin film in said plurality of thin films which is in contact with said resist film is made of a material containing at least one of elements with atomic numbers [[73]] 75 to 78 [[79]] by 50 wt% or greater and those other than said thin film contacting said resist film are made of a material containing at least one of elements with atomic numbers 21, 23, 25 to 36, 38 to 41, 43 to 48, 50 to 54, 56, 57, 72, 80 and [[80]] 82 to 83 by 50 wt% or greater.

9. (Currently Amended) The electron beam recording substrate according to claim 7, wherein that thin film in said plurality of thin films which is in contact with said resist film is made of a material containing at least one of elements with atomic numbers 21, 23, 25 to 36, 38 to 41, 43 to 48, 50 to 54, 56, 57, 72, 80 and [[80]] 82 to 83 by 50 wt% or greater and those other than said thin film contacting said resist film are made of a material containing at least one of elements with atomic numbers [[73]] 75 to 78 [[79]] by 50 wt% or greater.